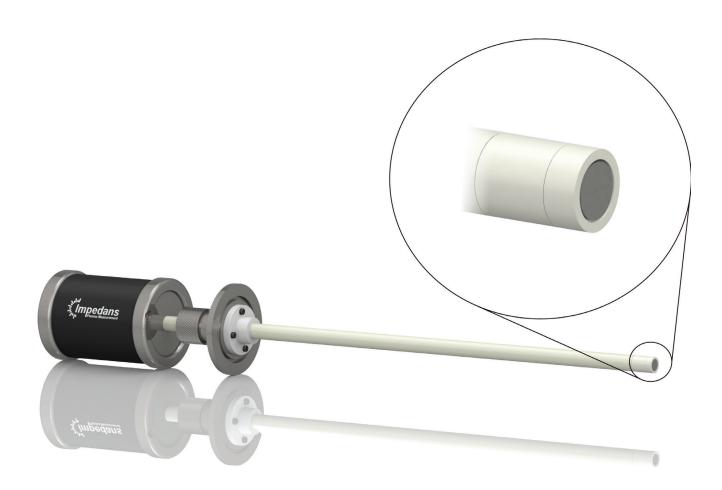
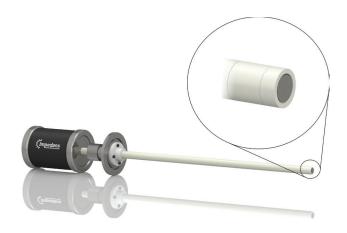
# Langmuir PlatoProbe™

**Deposition Tolerant Langmuir Probe** 





Langmuir Probe for Deposition Plasma Ultra-Fast Bias Planar Langmuir Probe Automated Pulsed Plasma Measurement Floating Potential
Plasma Density
Ion Current Density
Electron Temperature





The PlatoProbe™ is a planar Langmuir Probe designed to work in deposition plasmas even when an insulating film is deposited on the probe surface. The PlatoProbe™ is the first Langmuir probe on the market that can operate in plasmas with high deposition rates. A unique feature of The PlatoProbe™ is its ability to measure accurately key plasma parameters through a deposited layer several tens of microns thick. The deposition of insulating layers does not affect the accuracy of the probe measurement.

The PlatoProbe™ is a unique instrument enabling scientists to measure the electron density, lon density, electron temperature and floating potential of plasma including deposition plasma. The PlatoProbe™ provides plasma parameter measurement in DC, RF, Microwave, Continuous and Pulsed plasma. The PlatoProbe™ has the most advanced patented technology on the market using ultrafast biasing to penetrate the deposited film to obtain accurate measurements of the real plasma parameters in a wide range of plasma applications.

The PlatoProbe™ is used to establish plasma process repeatability, even in reactive gas plasma. It is the perfect instrument to understand plasma changes and the impact on surface treatment. The PlatoProbe™ is an essential plasma process diagnostic to understand the correlation between plasma inputs and the plasma state. The PlatoProbe™ reduces process and tool development time, as well as the time to market for new plasma products. Pulsed plasmas are used to tailor the electron or ion energy and The PlatoProbe™ is an integral part of such a process development.



### **Key Indicators**

Time Resolution	1μS
Plasma Power Source	DC, RF, Microwave, Continuous, Pulsed Plasma
Electron Density	1x10 <sup>6</sup> to 3x10 <sup>13</sup> cm <sup>-3</sup>
Ion Density	1x10 <sup>6</sup> to 3x10 <sup>13</sup> cm <sup>-3</sup>
Ion Current Density	1uA/cm² to 300mA/cm²
Electron Temperature	0.1 to 15 eV

#### **Benefits**

- Designed for Deposition Plasma
- Robust and Easy to Install
- Easy to Use Software
- Real Time Measurements
- Easy to Replace Probe Tips
- Custom Probe Shafts Available
- High Degree of Accuracy
- Key Instrument for Measuring Plasma Parameters
- Pulsed Power Compatible
- Broadband RF







### Specifications

Plasma Parameters	
Plasma Density	1x10 <sup>6</sup> to 3x10 <sup>13</sup> cm <sup>-3</sup>
Ion Current Density	1uA/cm² to 300mA/cm²
Electron Temperature	0.1 to 15 eV

Langmuir Probe	
Plasma Power Source	DC, RF, Microwave, Continuous, Pulsed Plasma
RF Plasma	Broadband Probe 2MHz to 100MHz
Probe Length	300mm to 1400mm (Custom Available)
Probe Diameter	9.5mm
Probe Tip Diameter	7mm
Customisation	On request
Maximum Operating Temperature	230°C

Electronics Control Unit			
Probe Voltage Scan Range	Floating potential ± 30V		
Current Range	100nA to 20mA		
Communication	USB 2.0		
Sampling Rate	80 MSPS (V,I)		
Data Acquisition Resolution	4.5mV, 4.5nA		
Time Resolved Step Resolution	1μS to 1mS		
External Trigger	TTL Compatible 10Hz to 50KHz		

Application Software	
Operating System	Windows 2000, XP, Vista, Windows 7





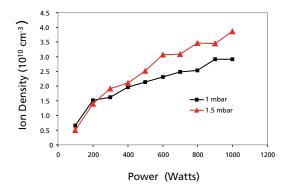
#### **Product Operating Parameter Table**

High	> 10 <sup>5</sup> Pa	>760 Torr	> 5000°	> 10 <sup>14</sup> cm <sup>-3</sup>	SiH <sub>4</sub>	Microwave (3 GHz - 20 GHz)
	1000Pa - 10⁵Pa	10 - 760 Torr	5000°	10 <sup>12</sup> - 10 <sup>14</sup> cm <sup>-3</sup>	C4F <sub>8</sub> , SF <sub>6</sub>	Microwave (1 GHz - 3 GHz)
	100Pa - 1000Pa	1 - 10 Torr	1000°	10 <sup>10</sup> - 10 <sup>12</sup> cm <sup>-3</sup>	CHF <sub>3</sub>	UHF (100 MHz - 1 GHz)
Medium	10Pa - 100Pa	0.1 - 1 Torr	500°	10 <sup>8</sup> - 10 <sup>10</sup> cm <sup>-3</sup>	Cl	RF (1 MHz - 100 MHz)
	1Pa - 10Pa	10 - 100 mTorr	200°	10 <sup>6</sup> - 10 <sup>8</sup> cm <sup>-3</sup>	O <sub>2</sub>	MF (0 - 1 MHz)
	0.1Pa -1Pa	1 - 10 mTorr	100°	10 <sup>4</sup> -10 <sup>6</sup> cm <sup>-3</sup>	N <sub>2</sub>	pDC (0 - 350 kHz)
Low	< 0.1 Pa	< 1 mTorr	20°	< 10 <sup>4</sup> cm <sup>-3</sup>	Ar, He	DC (0 kHz)
	Pressure (Pascal)	Pressure (Torr)	Gas Temperature	Density	Gas Reactivity	Power Frequency

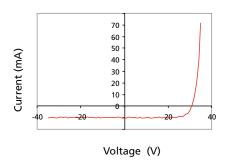
System Operating Parameters Beyond Operating Parameters

#### **Graphical Data**

# Measurement of ion density in Silane plasma using Langmuir Plato Probe™



## Real Current – Voltage characteristic of RF biased Planar Plato Probe



#### **Product Dimensions**



